

REMARKS

Claims remaining in the present patent application are numbered 8-10 and 12-15. Claim 11 has been canceled. The rejections and comments of the Examiner set forth in the Office Action dated November 29, 2005 have been carefully considered by the Applicants. Applicants respectfully request the Examiner to consider and allow the remaining claims.

Drawings

The drawings were objected to because the drawings are hand drawn. Applicants submit concurrently herewith formal drawings. The formal drawings have distinct labels, and as such, the objections to the drawings because of indistinct labels is moot at this time.

35 U.S.C. §102 Rejection

The present Office Action rejected Claims 8-13 under 35 U.S.C. 102(e) as being anticipated by Mehrad et al. (U.S. Patent No. 6,765,257). Applicants have reviewed the above cited references and respectfully submit that the present invention as recited in Claims 8-13, is neither anticipated nor rendered obvious by the Mehrad et al. reference.

Independent Claim 8

Applicants respectfully point out that independent Claim 8 recites that the present invention includes, in part:

a source contact coupled to said source column for providing electrical coupling with said plurality of source regions, said source contact located along a row of drain contacts coupled to drain regions of a row of memory cells that are arranged perpendicular to said source column, and wherein said source contact is of different dimension as each of said row of drain contacts.
(Emphasis Added)

The present invention pertains to a semiconductor memory device that includes an array of flash memory cells with a source line column for coupling to a plurality of common source lines, wherein the contact to the source line column facilitates straight word lines. In particular, independent Claim 8 recites that the source contact is located along a row of drain contacts, and is of a different dimension as each of the row of drain contacts.

Applicants respectfully note that the Mehrad et al. reference does not teach nor suggest the present semiconductor memory device that includes a source contact located along a row of drain contacts, wherein the source contact is of a different dimension than each of the row of drain contacts, as claimed in independent Claim 8 of the present invention.

In contrast to independent Claim 8 of the present invention, the Mehrad et al. reference, discloses FLASH EPROM cells in which an arsenic implant under the gate stack is performed in vertical source lines. The Mehrad et al. reference teaches that a source contact can be located in line with drain contacts. However, the Mehrad et al. reference specifically teaches that the source contact is of similar dimension as the drain contacts, as shown in Figure 1. This is in direct contrast to embodiments of the present invention in which the source contact is of a different dimension than each drain contact, as claimed in independent Claim 8 of the present invention.

Thus, Applicants respectfully submit that the present invention as disclosed in independent Claim 8 is not anticipated by the Mehrad et al. reference, and is in a condition for allowance. In addition, Applicants respectfully submit that Claims 9, 10, and 12-15 which depend from independent Claim 8 are also in a condition for allowance as being dependent on an allowable base claim.

35 U.S.C. §103 Rejection

The present Office Action rejected Claims 14 and 15 under 35 U.S.C. 103(a) as being unpatentable over Mehrad et

al. Applicants have reviewed the above cited reference and respectfully submit that the present invention as recited in Claims 14 and 15 is neither anticipated nor rendered obvious by the Mehrad et al. reference.

Applicants respectfully submit that the present invention as disclosed in dependent Claims 14 and 15 and 24 is not anticipated or rendered obvious by the Mehrad et al. reference since the claims depend on allowable base Claim 8, as previously discussed. In particular, the Mehrad et al. reference does not teach that the source contact is of different dimension than the drain contacts. As such, dependent Claims 14 and 15 are in a condition for allowance as being dependent on allowable base Claim 8.

CONCLUSION

In light of the amendments and arguments presented herein, Applicants respectfully request reconsideration of the rejected Claims for allowance thereof.

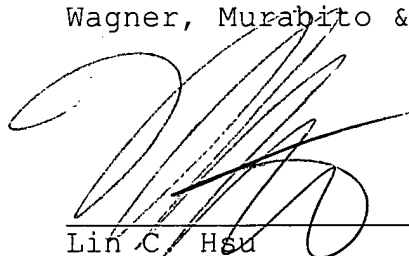
Based on the arguments presented above, Applicants respectfully assert that Claims 8-10 and 12-15 overcome the rejections of record. Therefore, Applicants respectfully solicit allowance of these Claims.

The Examiner is invited to contact Applicants' undersigned representative if the Examiner believes such action would expedite resolution of the present Application.

Respectfully submitted,

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